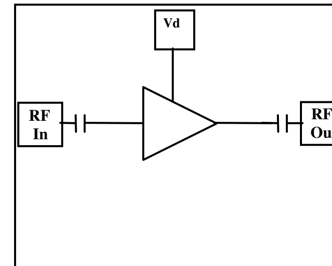
2 – 6 GHz 23dBm Medium Power Amplifier

Features

- Frequency Range : 2 – 6GHz
- 23 dBm output P1dB
- 10 dB Power gain
- 35% PAE
- High IP3
- Input Return Loss > 9dB
- Output Return Loss > 10dB
- Self bias operation
- No external matching required
- DC decoupled input and output
- 0.5 µm InGaAs pHEMT Technology
- Chip dimension: 1.6 x 1.6 x 0.1 mm

Functional Diagram



Typical Applications

- RADAR
- Military & space
- LMDS, VSAT

Description

The AMT2123041 is a 2-6GHz medium power amplifier with 23dBm power output. The MPA operates in 2–6GHz frequency range and features 10 dB of gain with input and output return losses of 9dB and 10dB respectively. The MPA has a high IP3 of 32dBm and 35% PAE. This feature enables it to be used in the applications requiring efficiency along with linearity. The chip operates with single bias supply voltage. The die is fabricated using a reliable 0.5µm InGaAs pHEMT technology. The Circuit grounds are provided through vias to the backside metallization.

Absolute Maximum Ratings (1)

Parameter	Absolute Maximum	Units
Drain bias voltage (Vd)	+9.5	volts
RF input power (RFin at Vd=8V)	23	dBm
Operating temperature	-50 to +85	^{o}C
Storage Temperature	-65 to +150	^{o}C

1. Operation beyond these limits may cause permanent damage to the component

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Electrical Specifications [1] @ T_A = 25 °C, V_d = 8V, Zo =50 Ω

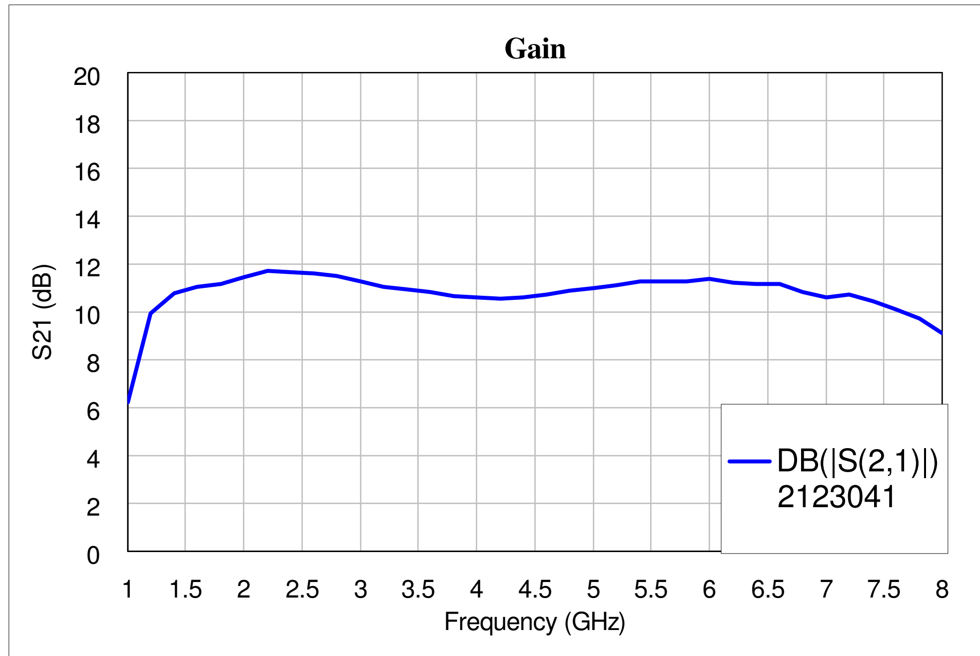
Parameter	Typ.	Units
Frequency Range	2 – 6	GHz
Gain	10	dB
Gain Flatness	+/-0.5	dB
Output Power (P1 dB)	23	dBm
Input Return Loss	9	dB
Output Return Loss	10	dB
Saturated output power (Psat)	25	dBm
Output Third Order Intercept (IP3)	32	dBm
Power Added Efficiency (PAE)	35%	--
Supply Current	90	mA

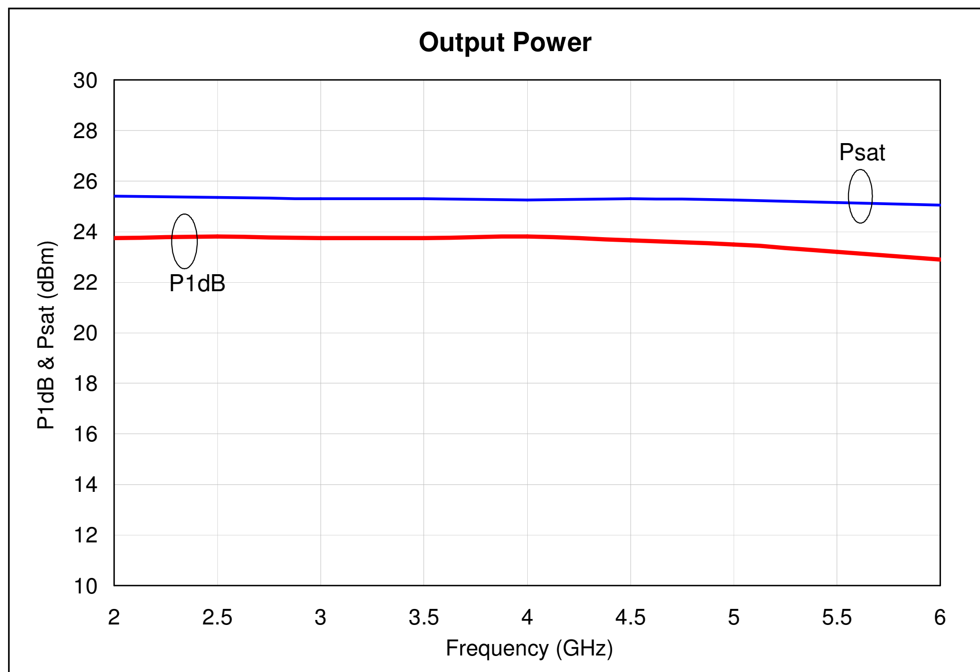
Note:

1. Electrical specifications as measured in test fixture.

Test fixture data

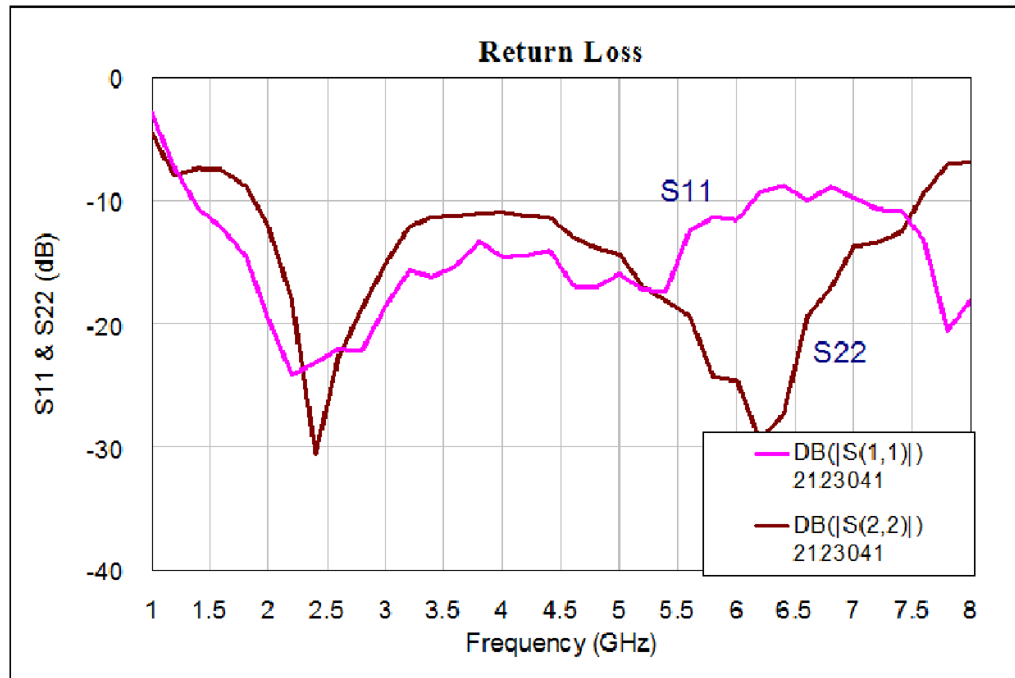
V_d = 8V, Total Current =90mA, T_A = 25 °C

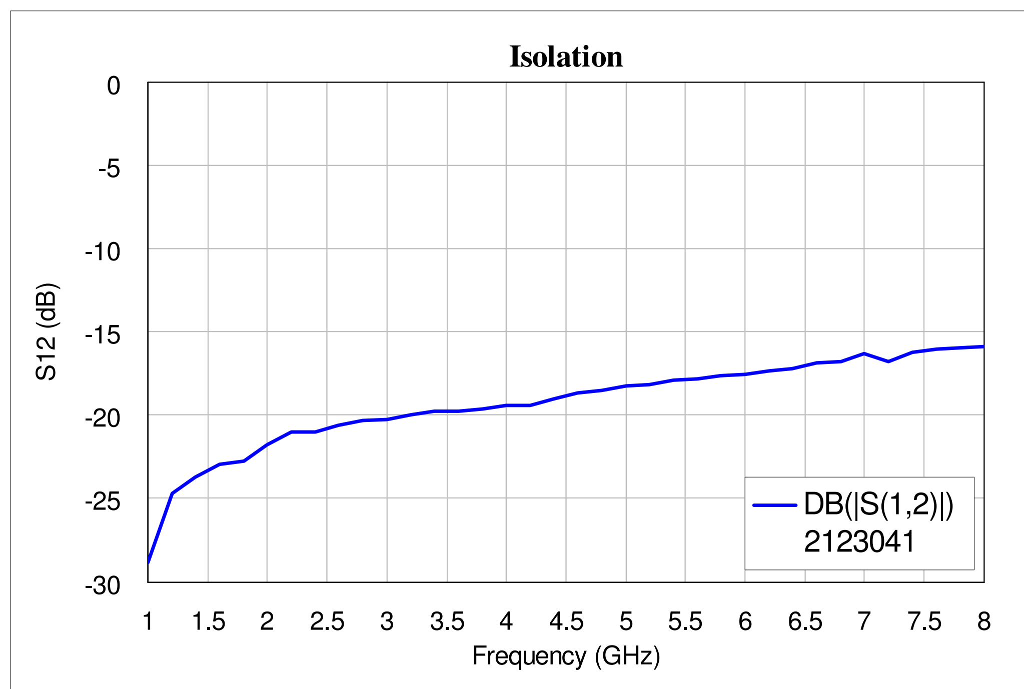




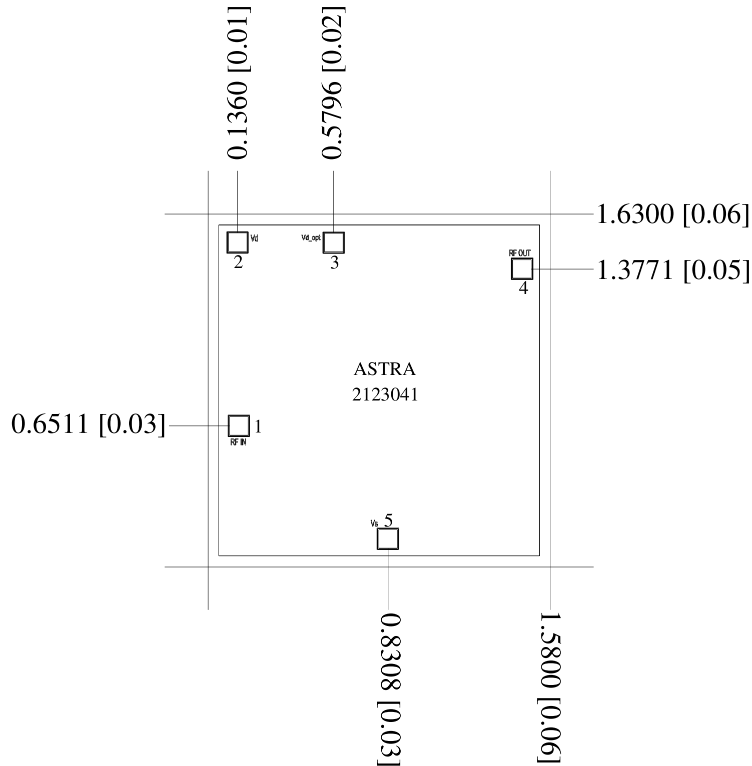
Test fixture data

V_d = 8V, Total Current =90mA, T_A = 25 °C





Bond Pad Locations

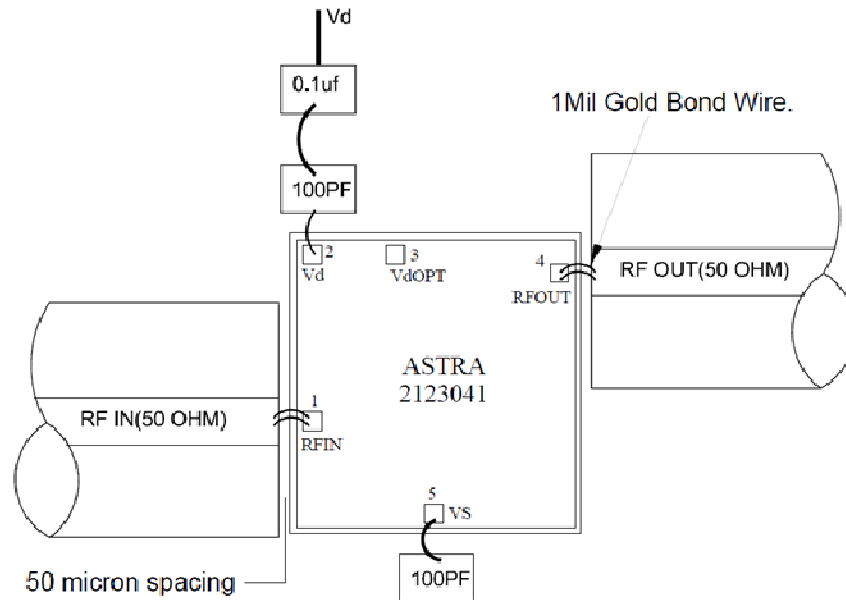


Units: millimeters

Note:

1. All RF and DC bond pads are 100µm x 100µm
2. Pad no. 1 : RF IN
3. Pad no. 2 : Drain Voltage(V_d)
4. Pad no. 4 : RF Output
5. Pad no. 5 : Source Bypass Single Layer Capacitor (100pF)

Recommended Assembly Diagram



Note:

1. Two 1 mil (0.0254mm) bond wires of minimum length should be used for RF input and output.
2. Two 1 mil (0.0254mm) bond wires of minimum length should be used from chip bond pad to 100pF Single Layer Bypass Capacitors as shown above.
3. Input and output 50 ohm lines are on 5 mil RT Duroid substrate.
4. 0.1 µF capacitors may be additionally used as a second level of bypass for reliable operation
5. The RF input & output ports are DC decoupled on-chip.
6. Proper heat sink like Copper tungsten or copper molybdenum to be used for better reliability of chip

Die attach: For Epoxy attachment, use of a two-component conductive epoxy is recommended. An epoxy fillet should be visible around the total die periphery. If Eutectic attachment is preferred, use of fluxless AuSn (80/20) 1-2 mil thick preform solder is recommended. Use of AuGe preform should be strictly avoided.

Wire bonding: For DC pad connections use either ball or wedge bonds. For best RF performance, use of 150 - 200µm length of wedge bonds is advised. Single Ball bonds of 250-300µm though acceptable, may cause a deviation in RF performance.

GaAs MMIC devices are susceptible to Electrostatic discharge. Proper precautions should be observed during handling, assembly & testing

All information and Specifications are subject to change without prior notice